

Evaluation of microstructural evolution of glassy carbon induced by helium implantation and annealing

Tuesday, 4 November 2025 13:44 (1 minute)

The effects of helium ion (He⁺2) implantation into glassy carbon (GC) were systematically investigated. He⁺2 ions with an energy range of 17 keV were implanted into GC to fluences of 10¹⁶, 10¹⁷, and 10¹⁸ cm⁻² at room temperature (RT). The as-implanted GC samples were subsequently vacuum annealed at 300 °C, 500 °C, and 800 °C for 1 hour. The structural evolution of GC was characterized using Raman spectroscopy and transmission electron microscopy (TEM). A fluence-dependent trend in displacement per atom (dpa) and He concentration was observed. Raman spectroscopy revealed progressive structural disorder and amorphization at fluences of 10¹⁷ and 10¹⁸ cm⁻², marked by merging and redshifts of the D and G peaks, indicating tensile strain in the carbon matrix. Partial recovery of D/G peak separation and crystalline order was observed, especially at 800 °C for the 10¹⁶ cm⁻² fluence. TEM micrographs showed a confined damaged region of about 130 nm, with distinct defect aggregation towards the bulk for fluences of 10¹⁶ and 10¹⁷ cm⁻², whereas the defect aggregation appeared in two channels for the fluence of 10¹⁸ cm⁻². At a fluence of 10¹⁷ cm⁻², nonlinear dispersion and saturation effects were observed. Overall, annealing facilitated partial microstructural recovery, particularly for samples with fluences of 10¹⁶ and 10¹⁷ cm⁻² at 800 °C.

Technical Track

Fuel Cycle and Waste Management

Primary author: ISMAIL, Mahjoub Yagoub Abdalla (Department of Physics, University of Pretoria, South Africa)

Co-authors: Mrs MAEPA, Charity (Department of Physics, University of Pretoria, South Africa); Prof. NJOROGE, Eric (Department of Physics, University of Pretoria, South Africa); Prof. HLATSHWAYO, Thulani (Department of Physics, University of Pretoria, South Africa); Dr ABDALLA, Zaki (Department of Physics, University of Pretoria, South Africa)

Session Classification: Poster